

AMENDMENTS

This listing of claims will replace all prior versions, and listings, of claims in the application:

In the Claims:

1. (Cancelled)
2. (Currently Amended) ~~[[The]]~~ A local dry etching apparatus according to Claim 1: for removing unevenness on a surface of a semiconductor wafer, comprising:
a nozzle from which a gas including an activated species produced by a plasma is injected locally to the surface of the semiconductor wafer; and
a wafer table supporting the semiconductor wafer concentrically thereon, a radius of the wafer table being larger than a radius of the semiconductor wafer

wherein a ~~value produced by subtracting~~ difference between the radius of ~~[[said]]~~ the semiconductor wafer ~~[[from]]~~ and the radius of ~~[[said]]~~ the wafer table is ~~large by an amount of~~ 10 percent ~~through to~~ to 40 percent ~~[[with]]~~ of a half value width of an etching rate distribution peak of said injected the gas injected from the nozzle.
3. (Currently Amended) The local dry etching apparatus ~~according to Claim 1: of claim~~ 2, wherein the radius of said wafer table is larger than the radius of said semiconductor wafer by 4 mm ~~through to~~ to 10 mm.
4. (Withdrawn) A local dry etching method for removing unevenness on a surface of a semiconductor wafer by blowing a gas including an activated species produced by a plasma and injected from a nozzle locally to the surface of the semiconductor wafer supported on a wafer table concentrically therewith:

wherein the radius of said wafer table is made larger than the radius of the semiconductor wafer.

5. (Withdrawn) The local dry etching method according to Claim 4:

wherein a value produced by subtracting the radius of said semiconductor wafer from the radius of said wafer table is made large by an amount of 10 percent through 40 percent with a half value width of an etching rate of said injected gas as a reference.

6. (Withdrawn) The local dry etching method according to Claim 4:

wherein the radius of said wafer table is made larger than the radius of said semiconductor wafer by 4 mm through 10 mm.

7. (Cancelled) A wafer table for a local dry etching apparatus for removing unevenness on a surface of a semiconductor wafer by blowing a gas including an activated species produced by a plasma and injected from a nozzle locally to the surface of the semiconductor wafer supported on a wafer table concentrically therewith:

wherein said wafer table is provided with a supporting face in a circular shape and a radius larger than a radius of the semiconductor wafer supported by the supporting face.

8. (Currently Amended) ~~[[The]]~~ A wafer table according to Claim 7: for a local dry etching apparatus for removing unevenness on a surface of a semiconductor wafer by injecting a gas including an activated species produced by a plasma through a nozzle locally to the surface of the semiconductor wafer supported on and concentric with the wafer table,

wherein a radius of the wafer table is configured to be larger than a radius of the semiconductor wafer supported on the wafer table so that a ~~wherein the wafer table is provided with the radius in which a value produced by subtracting~~ difference between the radius of ~~[[said]]~~ the semiconductor wafer ~~[[from]]~~ and the radius of ~~[[said]]~~ the wafer table is large by an

amount of 10 percent through to 40 percent ~~[[with]]~~ of a half value width of an etching rate distribution peak of ~~said injected~~ the gas injected from the nozzle ~~as a reference~~.

9. (Currently Amended) The wafer table ~~according to Claim 7:~~ of claim 8, wherein the radius of the wafer table is ~~provided with the radius~~ larger than the radius of said semiconductor wafer by 4 mm ~~through to~~ to 10 mm.